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JAPANESE PATENT OFFICE

PATENT ABSTRACTS OF JAPAN

(11) Publication number: 05159585 A

(43) Date of publication of application: 25.06.1993

(51) Int. Cl G11C 16/02

G11C 5/00, G11C 11/22, H01L 27/115, H01L 29/784, H01L 29/788,
H01L 29/792

(21) Application number: 03325543

(22) Date of filing: 10.12.1991

(71) Applicant: HITACHI LTD

(72) Inventor: ABE YOSHIO
WAKAGI MASATOSHI
KOZONO YUZO
MINEMURA TETSUO

(54) SOLID-STATE STORAGE ELEMENT

tive substrate of a card size.

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(57) Abstract:

PURPOSE: To obtain easily a thin, lightweight memory card having a large capacity by using a thin-film transistor formed on an insulative substrate for a memory circuit.

CONSTITUTION: A solid-state storage element is composed of an electronic circuit constructed of a thin-film transistor TFT 13, a ferroelectric capacitor 14, etc., formed on an insulative substrate and of a protective film 11 for protecting the circuit from external environment, sealing resin 12 and an oversheet 2. The circuit construction of a memory cell is made up of the thin-film transistor TFT 13 and the ferroelectric capacitor 14. Since polarization remains in a ferroelectric even when no voltage is impressed, it can keep a stored content without a power source. Since this solid-state storage element is light in weight and thin and necessitates no power source at the time of stoppage, it can be used as a memory card by forming it on the insula-

